2SK3018W

General Description

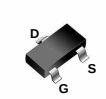
These N-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

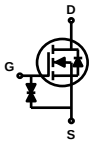
Features

30V,250mA, RDS(ON) =1.5Ω@VGS = 10V
Improved dv/dt capability
Fast switching
Green Device Available

Applications

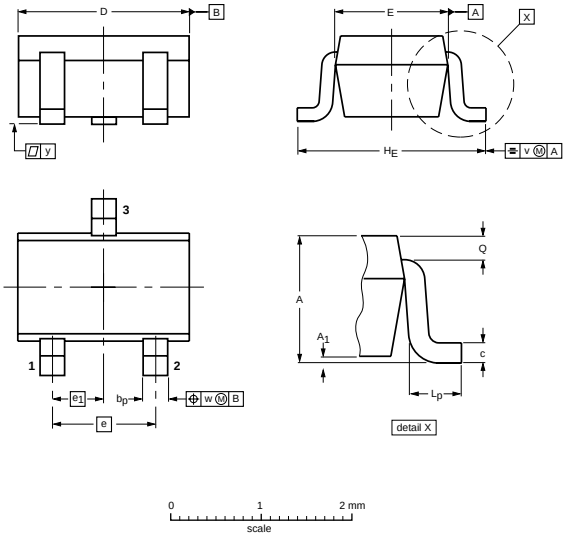
Notebook
Load Switch
Battery Protection
Hand-held Instruments





BVDSS	RDSON	ID
30V	1 .5Ω	250mA

SOT-323



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1 max	b_p	c	D	E	e	e_1	H_E	L_p	Q	v	w
mm	1.1 0.8	0.1	0.4 0.3	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.23 0.13	0.2	0.2

Absolute Maximum Ratings Tc=25℃ unless otherwise noted

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	±20	V
I_D	Drain Current – Continuous (T_A=25˚C)	250	mA
	Drain Current – Continuous (T_A=70˚C)	200	mA
I_{DM}	Drain Current – Pulsed[1]	1.0	A
P_D	Power Dissipation (T_C=25˚C)	300	mW
	Power Dissipation – Derate above 25˚C	2.4	mW/˚C
T_{STG}	Storage Temperature Range	-55 to 150	˚C
T_J	Operating Junction Temperature Range	-55 to 125	˚C

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	400	˚C/W

2SK3018W

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	30	---	---	V
$\triangle BV_{DSS}/\triangle T_J$	BV_{DSS} Temperature Coefficient	Reference to 25℃ , I_D=1mA	---	0.05	---	V/℃
I_{DSS}	Drain-Source Leakage Current	V_{DS}=30V , V_{GS}=0V , T_J=50℃	---	---	100	nA
		V_{DS}=30V , V_{GS}=0V , T_J=85℃	---	---	400	nA
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±6	uA

On Characteristics

$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V , I_D=0.3A	---	1.5	3	Ω
		V_{GS}=4.5V , I_D=0.2A	---	1.6	4	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	0.8	1.1	1.6	V
$\triangle V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	3	---	mV/℃

Dynamic and switching Characteristics

C_{iss}	Input Capacitance	V_{DS}=30V , V_{GS}=0V , F=1MHz	---	20	---	pF
C_{oss}	Output Capacitance		---	12	---	
C_{rss}	Reverse Transfer Capacitance		---	6	---	

Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	V_G=V_D=0V , Force Current	---	---	250	mA
I_{SM}	Pulsed Source Current		---	---	500	mA
V_{SD}	Diode Forward Voltage	V_{GS}=0V , I_S=0.2A , T_J=25℃	---	---	1.2	V

Note :
1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%.
3. Essentially independent of operating temperature.

RATING AND CHARACTERISTIC CURVES (2SK3018W)

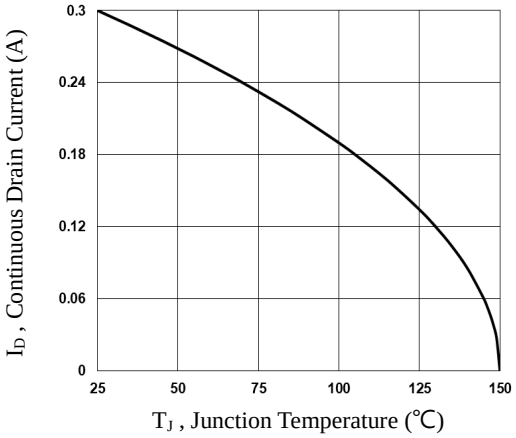


Fig.1 Continuous Drain Current vs. T_C

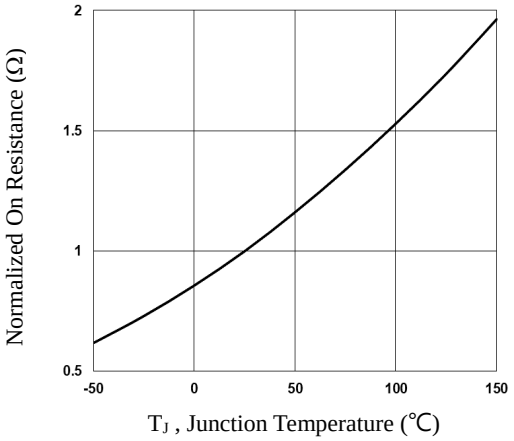


Fig.2 Normalized RDSON vs. T_J

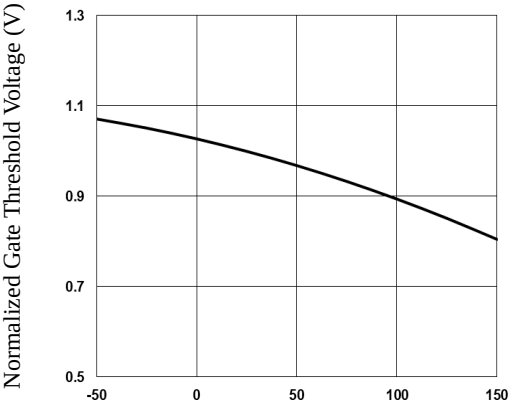


Fig.3 Normalized V_{th} vs. T_J

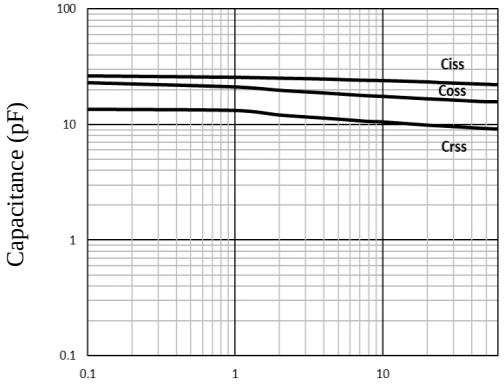


Fig.4 Capacitance Characteristics

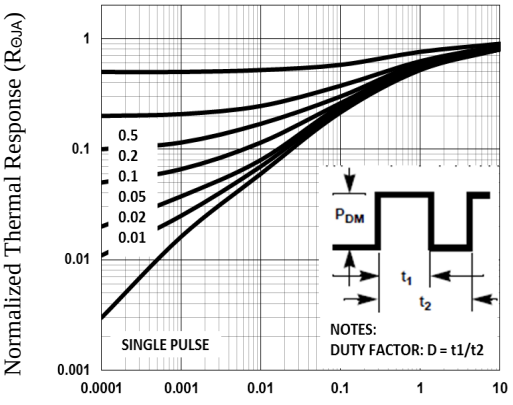


Fig.5 Normalized Transient Response

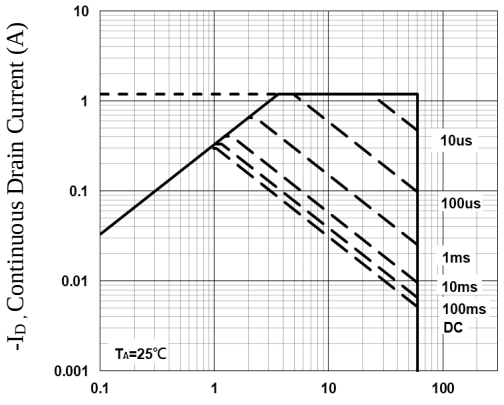


Fig.6 Maximum Safe Operation Area

RATING AND CHARACTERISTIC CURVES (2SK3018W)

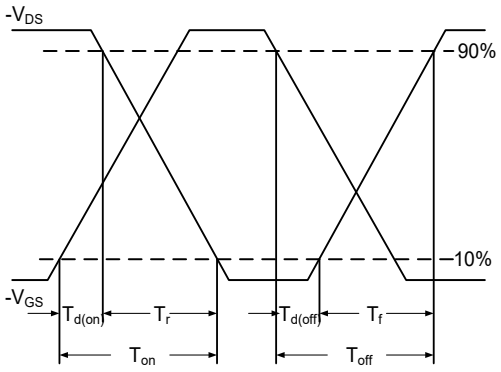


Fig.7 Switching Time Waveform

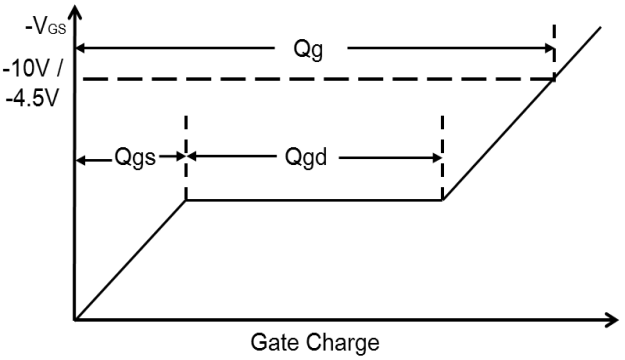


Fig.8 Gate Charge Waveform